Method of Fabricating Patterned Device Using Sacrificial Spacer Layer

Features

The precise gaps that constitute the most difficult step of the method have been demonstrated

Description

Providing precise line width control of patterned optoelectronic and microelectronic devices. This technology should be useful for applications requiring nanometer precision features.

Nanometer tolerance shadow masks can be made using the conventional deposition and etch steps of low-resolution lithographic techniques. This method enables the fabrication of line widths and features with a resolution appreciably finer than the Rayleigh limit.

Remarks

- US Patent No. 7,442,577
- Alias: None
- NSA Reference number 1442

Potential Applications

The fabrication method reduces cost by enabling nanometer feature definition without requiring expensive e-beam or deep UV lithography.

Contact Information

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